



SAMSUNG ELECTRONICS AMERICA, INC.
American QA Lab
18600 Broadwick St.
Rancho Dominguez, CA 90220

DATE: June 05, 2008

Federal Communications Commission
Authorization and Evaluation Division
7435 Oakland Mills Road
Columbia, MD21046

Attn : OET Dept.

SUBJECT: **Samsung Electronics Co., Ltd.**
FCC ID: A3LSMT-I8120
Class II Permissive Change
Orig. Grant Date: March 10, 2008

Gentlemen:

Transmitted herewith is an application for a Class II Permissive Change Certification of the A3LSMT-I8120.

The device is identical to the previously certified A3LSMT-I8120 except for the proposed modifications which include following changes.

The changes filed under this application are:

- 1) Modifying the DECT antennas with higher gain in 1.92GHz ~1.93GHz.
But we assure that it won't produce any side effect to RF portion or total gain.
- Gain change: 2.75 dBi (old) → 3.169 dBi (new)
- 2) Changing some components Handset for TIA standard
- 3) Modified PCB layout to accommodate the changing components.
- 4) Minor EMI changes.

Should you have any questions or comments concerning the above, please contact the undersigned.

Sincerely,

A handwritten signature in black ink, appearing to read "A. J. Kim".

Steve Kim
General Manager
American QA Lab
SAMSUNG Electronics America INC.